

# BYV410-600 Dual enhanced ultrafast power diode Rev. 2 — 5 August 2011

Product data sheet

### **Product profile** 1.

## 1.1 General description

Dual enhanced ultrafast power diode in a SOT78 (TO-220AB) plastic package.

## 1.2 Features and benefits

- High thermal cycling performance
- Low on state losses

- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations

## 1.3 Applications

■ Dual mode (DCM and CCM) PFC

■ Power Factor Correction (PFC) for Interleaved Topology

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\bar{\delta} = 0.5$ ; $T_{mb} \le 92$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	20	Α
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	1.4	2.1	V
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 5	-	20	35	ns
Q <sub>r</sub>	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	15	28	nC



## Dual enhanced ultrafast power diode

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		K
mb	Κ	mounting base; cathode	1 2 3	sym125
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV410-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## **Dual enhanced ultrafast power diode**

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		- , , , , , , , , , , , , , , , , , , ,			
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta$ = 0.5; $T_{mb} \le 92$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	20	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb}$ ≤ 108 °C; per diode	-	20	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	132	Α
		$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	120	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

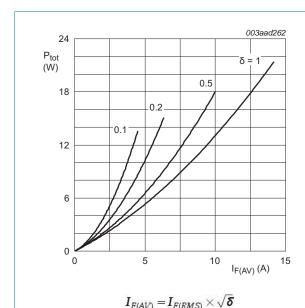
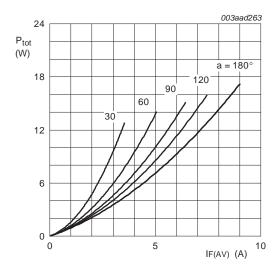


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a =form factor  $= I_{T(RMS)} / I_{T(AV)}$ 

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

## Dual enhanced ultrafast power diode

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 3	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

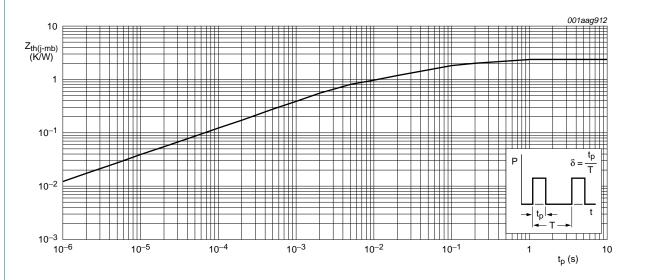


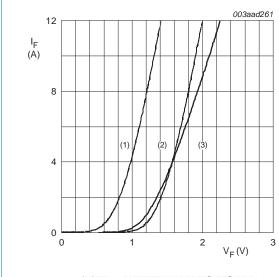
Fig 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

## Dual enhanced ultrafast power diode

# 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 4	-	1.4	2.1	V
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 600 V	-	13	50	μA
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1	1.5	mΑ
Dynamic ch	naracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	15	28	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; see Figure 5	-	20	35	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; see Figure 5	-	1.4	1.9	Α
$V_{FR}$	forward recovery voltage	$I_F = 1 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; see Figure 6	-	3.2	-	V



(1)  $T_j = 150 \, ^{\circ}C$ ; typical values (2)  $T_j = 150 \, ^{\circ}C$ ; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig 4. Forward current as a function of forward voltage

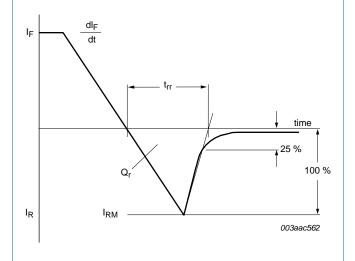
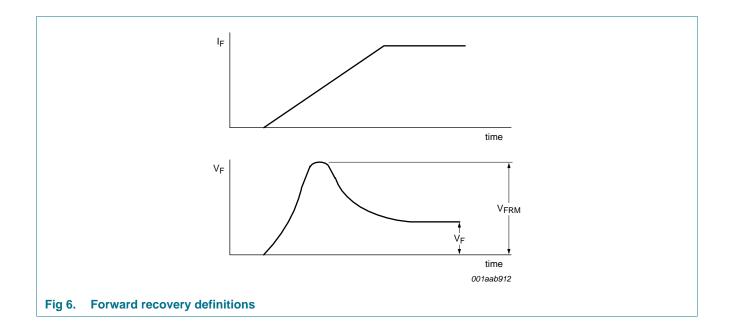


Fig 5. Reverse recovery definitions; ramp recovery

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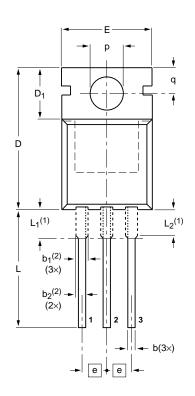
# Dual enhanced ultrafast power diode

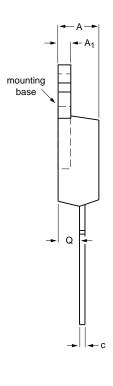


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# 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78





0 5 10 mm

## DIMENSIONS (mm are the original dimensions)

UNIT	ГА	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q	
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig 7. Package outline SOT78 (TO-220AB)

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# Dual enhanced ultrafast power diode

# **Revision history**

#### Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV410-600 v.2	20110805	Product data sheet	-	BYV410-600_1
Modifications:	<ul> <li>Various changes to</li> </ul>	content.		
BYV410-600_1	20090629	Product data sheet	-	-

## Dual enhanced ultrafast power diode

# 9. Legal information

## 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## Dual enhanced ultrafast power diode

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